

## SP6T PIN Diode Switch with Integrated Bias Network 2 - 18GHz

Rev. V2

### Features

- Ultra Broad Bandwidth: 2GHz to 18GHz
- 1.9dB Insertion Loss, 35dB Isolation at 18GHz
- Reliable. Fully Monolithic, Glass Encapsulated Construction

### Description

The MA4SW610B-1 is a reflective SP6T series shunt broad band switch with integrated bias networks made with M/A-COM's HMIC™ (Heterolithic Microwave Integrated Circuit) process, US Patent 5,268,310. This process allows the incorporation of silicon pedestals that form series and shunt diodes or vias by imbedding them in low loss, low dispersion glass. By using small spacing between elements, this combination of silicon and glass gives HMIC devices low loss and high isolation performance through 18 GHz.

### Applications

These high performance switches are suitable for the use in multi-band ECM, Radar, and instrumentation control circuits where high isolation to insertion loss ratios are required. With a standard +5V/-5V, TTL controlled PIN diode driver, 80ns switching speeds are achieved.

### Absolute Maximum Ratings<sup>1</sup>

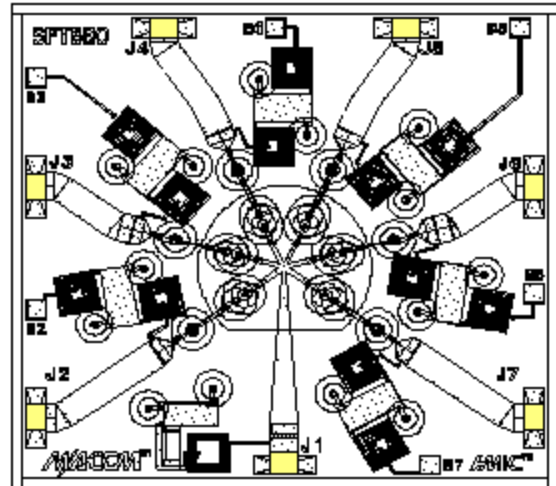
@ T<sub>AMB</sub> = +25°C (unless otherwise specified)

| Parameter                 | Value           |
|---------------------------|-----------------|
| Operating Temperature     | -65°C to +125°C |
| Storage Temperature       | -65°C to +150°C |
| RF CW Incident Power      | +30dBm          |
| DC Bias Current (Forward) | +/- 20mA        |
| Applied Voltage (Reverse) | 15V             |

#### Note:

- 1) Exceeding any of these values may result in permanent damage.

### MA4SW610B-1 Layout



### Nominal Chip Dimensions

| Chip Dimensions (mm)         |       |       |
|------------------------------|-------|-------|
|                              | X     | Y     |
| Chip                         | 3370  | 3120  |
| Pad Dimensions (mm)          |       |       |
|                              | X     | Y     |
| RF                           | 400   | 125   |
| DC                           | 125   | 125   |
| Pad Locations (mm)           |       |       |
|                              | X     | Y     |
| J1                           | 0     | 0     |
| J2                           | -1535 | +300  |
| B2                           | -1535 | +1000 |
| J3                           | -1535 | +1800 |
| B3                           | -1535 | +2500 |
| J4                           | -750  | +2820 |
| B4                           | -50   | +2820 |
| J5                           | +750  | +2820 |
| B5                           | +1450 | +2820 |
| J6                           | +1535 | +1800 |
| B6                           | +1535 | +1100 |
| J7                           | +1535 | +300  |
| B7                           | +900  | 0     |
| Pad Locations Relative to J1 |       |       |

#### Notes:

- 1) Topside and backside metallization is gold, 2.5µm thick typical.
- 2) Yellow areas indicate bondpads

**ADVANCED:** Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

**PRELIMINARY:** Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

- **North America** Tel: 800.366.2266 / Fax: 978.366.2266
  - **Europe** Tel: 44.1908.574.200 / Fax: 44.1908.574.300
  - **Asia/Pacific** Tel: 81.44.844.8296 / Fax: 81.44.844.8298
- Visit [www.macomtech.com](http://www.macomtech.com) for additional data sheets and product information.

M/A-COM Technology Solutions Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

## Electrical Specifications @ $T_A = 25\text{ }^\circ\text{C}$ , +/- 10 mA Bias Current (On-Wafer Measurements)

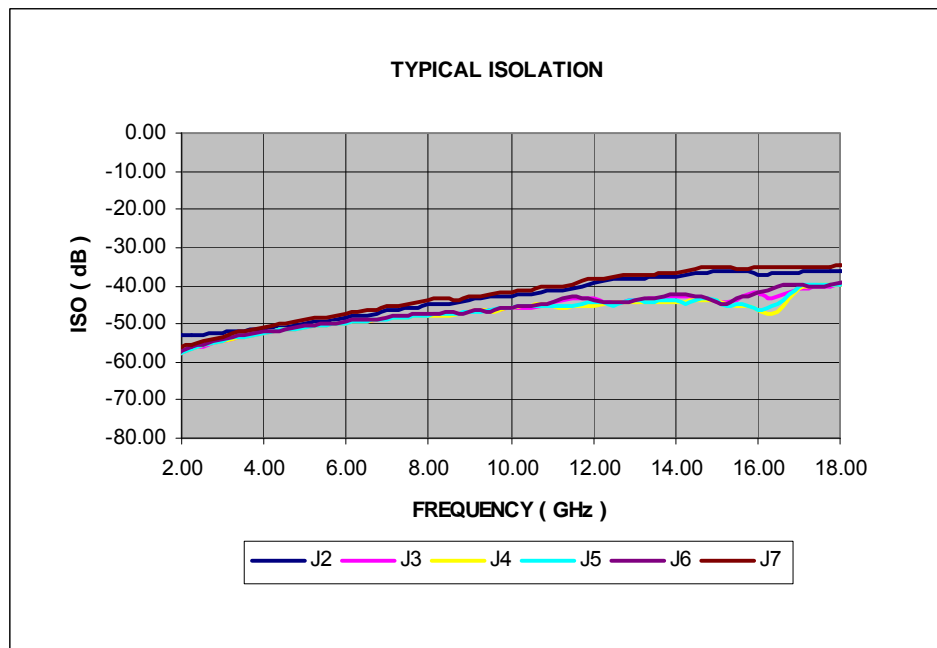
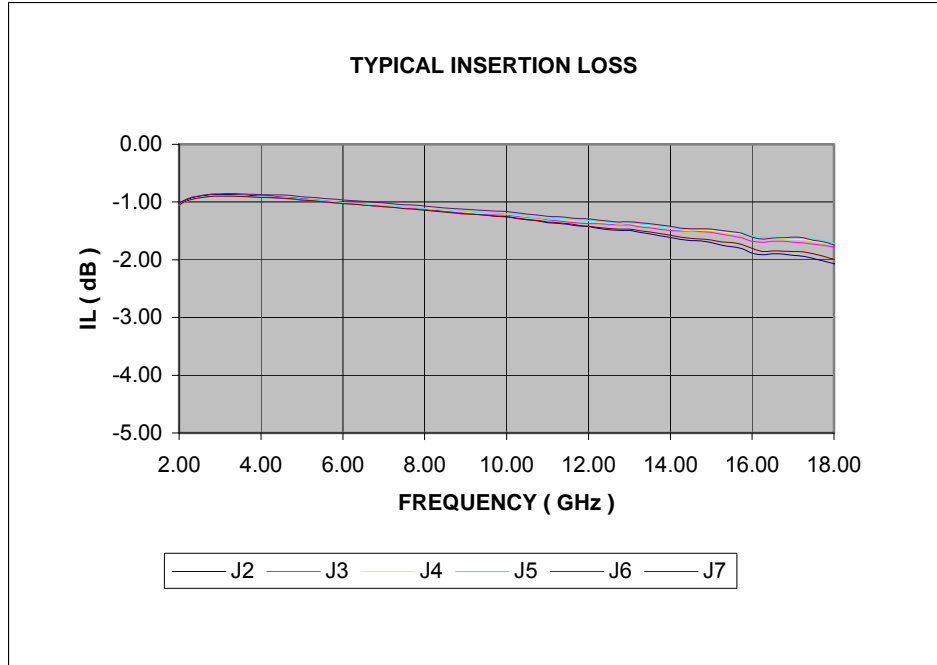
| Parameters                   | Frequency | Minimum | Typical | Maximum | Units |
|------------------------------|-----------|---------|---------|---------|-------|
| Insertion Loss               | 6 GHz     | -       | 1.0     | 1.4     | dB    |
|                              | 12 GHz    | -       | 1.3     | 2.0     | dB    |
|                              | 18 GHz    | -       | 1.9     | 2.9     | dB    |
| Isolation                    | 6 GHz     | 43      | 49      | -       | dB    |
|                              | 12 GHz    | 35      | 43      | -       | dB    |
|                              | 18 GHz    | 30      | 39      | -       | dB    |
| Input Return Loss            | 6 GHz     | -       | 18      | -       | dB    |
|                              | 12 GHz    | -       | 20      | -       | dB    |
|                              | 18 GHz    | -       | 16      | -       | dB    |
| Output Return Loss           | 6 GHz     | -       | 19      | -       | dB    |
|                              | 12 GHz    | -       | 22      | -       | dB    |
|                              | 18 GHz    | -       | 20      | -       | dB    |
| Switching Speed <sup>1</sup> | 10 GHz    | -       | 80      | -       | nS    |

1. Typical switching speed is measured from 10% to 90% of the detected RF voltage driven by a TTL compatible driver. Driver output parallel RC network uses a capacitor between 390pF - 560pF and a resistor between 150 - 220Ω to achieve 80ns rise and fall times.

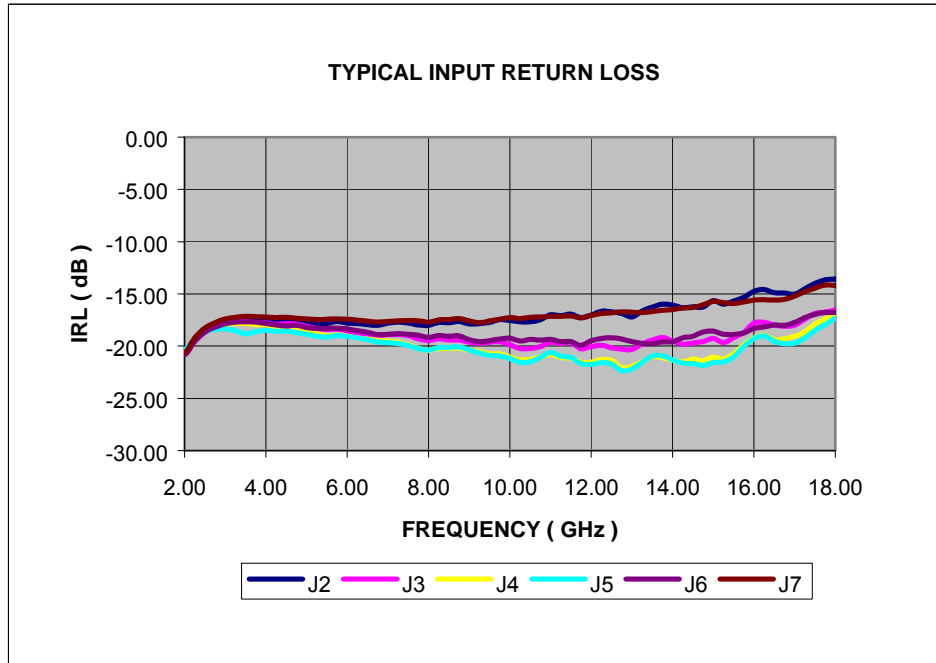
## Typical Driver Connections

| Control Level (DC Current) |        |        |        |        |        | Condition of RF Output |           |           |           |           |           |
|----------------------------|--------|--------|--------|--------|--------|------------------------|-----------|-----------|-----------|-----------|-----------|
| B2                         | B3     | B4     | B5     | B6     | B7     | J2-J1                  | J3-J1     | J4-J1     | J5-J1     | J6-J1     | J7-J1     |
| -10 mA                     | +10 mA | +10 mA | +10 mA | +10 mA | +10 mA | Low Loss               | Isolation | Isolation | Isolation | Isolation | Isolation |
| +10 mA                     | -10 mA | +10 mA | +10 mA | +10 mA | +10 mA | Isolation              | Low Loss  | Isolation | Isolation | Isolation | Isolation |
| +10 mA                     | +10 mA | -10 mA | +10 mA | +10 mA | +10 mA | Isolation              | Isolation | Low Loss  | Isolation | Isolation | Isolation |
| +10 mA                     | +10 mA | +10 mA | -10 mA | +10 mA | +10 mA | Isolation              | Isolation | Isolation | Low Loss  | Isolation | Isolation |
| +10 mA                     | +10 mA | +10 mA | +10 mA | -10 mA | +10 mA | Isolation              | Isolation | Isolation | Isolation | Low Loss  | Isolation |
| +10 mA                     | +10 mA | +10 mA | +10 mA | +10 mA | -10 mA | Isolation              | Isolation | Isolation | Isolation | Isolation | Low Loss  |

## Typical R.F. Microwave Performance



## Typical R.F. Microwave Performance



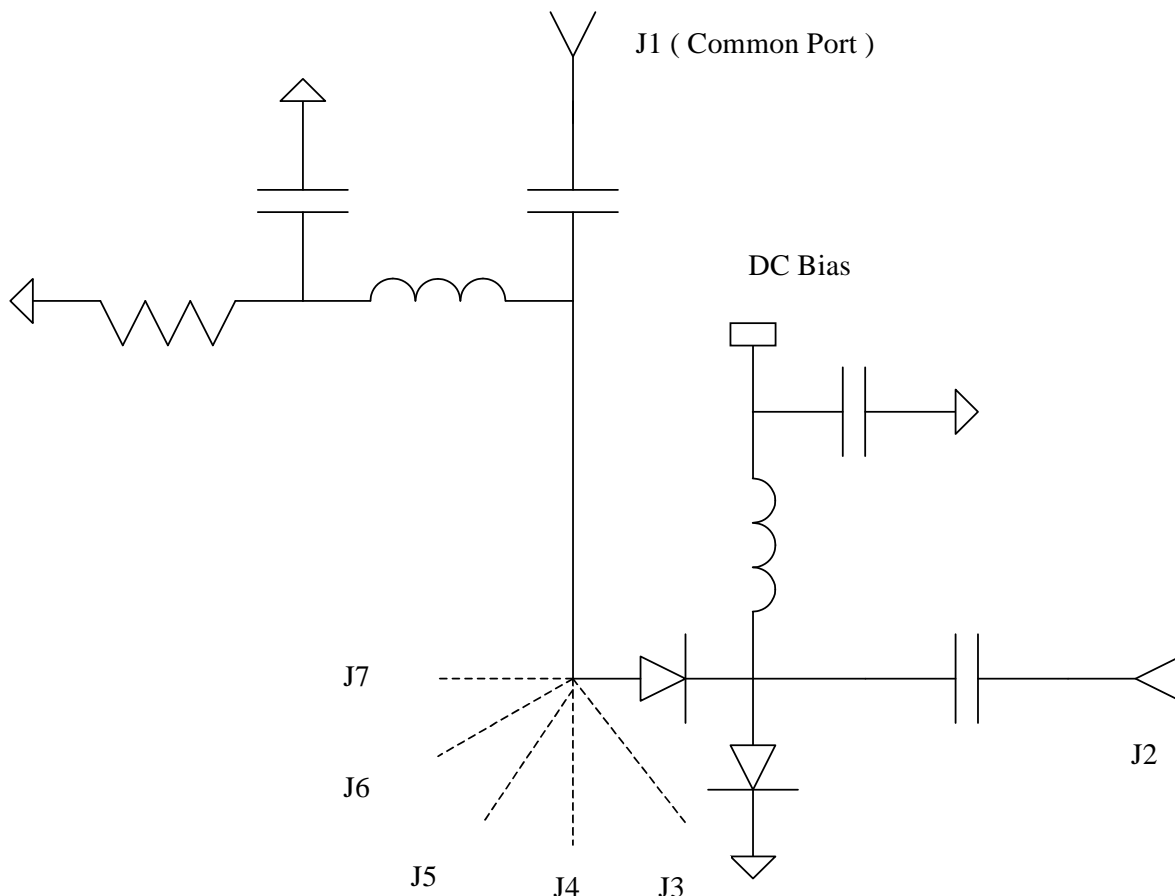
## Operation of the MA4SW610B-1 Switch

The simultaneous application of negative DC current to the low loss port and positive DC current to the remaining isolated ports as shown in the schematic provides successful RF operation of the MA4SW Series of PIN Diode Switches. The backside area of the die is the RF and DC return ground plane. The DC bias return is located on common port J1. Constant current sources should supply the DC control currents.

In the low loss state, the series diode must be forward biased and the shunt diode reverse biased. For all isolated ports, the shunt diode is forward biased while the series diode is reverse biased.

This design improves insertion loss, P1dB, IP3, and switching speed by incorporating a voltage pull-up resistor (~100  $\Omega$ ) in the DC return path, J1, under insertion loss Bias. A Typical Value of  $|-3\text{ V}|$  is achieved at the Insertion Loss Bias Node using  $\pm 20\text{ mA}$ , with a Standard,  $\pm 5\text{ V}$  TTL Controlled PIN Diode Driver.

### MA4SW610B-1 Schematic



## Assembly Considerations

The following precautions should be observed for successful assembly of the die.

## Cleanliness

These chips should be handled in a clean environment free of dust and contaminants.

## Electro-Static Sensitivity

The MA4SW Series PIN switches are ESD, Class 1 sensitive. The proper ESD handling procedures should be used.

## Wire Bonding

Thermosonic wedge wire bonding using 0.003" x 0.00025" ribbon or 0.001" diameter gold wire is recommended. A stage temperature of 150°C and a force of 18 to 22 grams should be used. Ultrasonic energy should be adjusted to the minimum required to achieve a good bond. RF bonds should be as short as possible to minimize inductance.

## Mounting

These chips have Ti-Pt-Au back metal. They can be die mounted with a 80Au/20Sn or Sn62/Pb36/Ag2 solder preform or electrically conductive Ag epoxy. Mounting surface must be clean of oils and contaminants and flat.

## Eutectic Die Attachment

An 80/20 gold-tin eutectic solder preform is recommended with a work surface temperature of 255 °C and a tool tip temperature of 265°C. When hot gas is applied, the tool tip temperature should be 290 °C. The chip should not be exposed to temperatures greater than 320°C for more than 10 seconds. No more than 3 seconds should be required for the attachment.

## Epoxy Die Attachment

Assembly should be preheated to 125-150°C. A Controlled thickness of 2 mils is recommended for best electrical and thermal conductivity. A thin epoxy fillet should be visible around the perimeter of the chip after placement. Cure epoxy per manufacturer's recommended schedule.

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: [org@lifeelectronics.ru](mailto:org@lifeelectronics.ru)